

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claims 1-46 (Canceled)

Claim 47 (Previously presented): The semiconductor die of claim 67, wherein said tip structure is integrally formed with said one of the interconnection elements.

Claim 48 (Previously presented): The semiconductor die of claim 67, wherein said one of the interconnection elements comprises a buckling beam interconnection element.

Claim 49 (Previously presented): The semiconductor die of claim 67, wherein said one of the interconnection elements is resilient.

Claims 50 and 51 (Canceled)

Claim 52 (Previously presented): The semiconductor die of claim 67, wherein said blade comprises a sharpened edge along said length thereof.

Claim 53 (Previously presented): The semiconductor die of claim 67, wherein said tip structure comprises at least one of palladium, cobalt, rhodium, tungsten, or diamond.

Claim 54 (Previously presented): The semiconductor die of claim 67, wherein said tip structure comprises a material comprising a spring alloy.

Claim 55 (Previously presented): The semiconductor die of claim 67, wherein said tip structure is secured to said one of the interconnection elements by one of braze or solder.

Claims 56-59 (Canceled)

Claim 60 (Currently amended): A semiconductor die tested by making temporary electrical connections between interconnection elements of a contactor device and terminals of the die, the method of making the temporary electrical connections comprising:

forcing into contact ones of the terminals and blades of ones of the interconnection elements ~~and ones of the terminals~~,

the blades deflecting across the terminals in a motion that is within plus or minus forty-five degrees of an axis corresponding to a length of the blade.

Claim 61 (Previously presented): The semiconductor die of claim 60, wherein the deflecting motion is within plus or minus thirty degrees of the axis corresponding to the length of the blade.

Claim 62 (Previously presented): The semiconductor die of claim 60, wherein the deflecting motion is approximately parallel to the axis corresponding to the length of the blade.

Claim 63 (Previously presented): The semiconductor die of claim 60, wherein the blades cut through oxide layers formed on the terminals.

Claim 64 (Previously presented): The semiconductor die of claim 60, wherein the blades cut into the terminals.

Claim 65 (Previously presented): The semiconductor die of claim 60, wherein the blades are sharpened.

Claim 66 (Previously presented): The semiconductor die of claim 60, wherein the blades comprise a truncated pyramid shape.

Claim 67 (Previously presented): The semiconductor die of claim 60, wherein each of the blades composes a tip structure disposed on one of the interconnection elements.

Claim 68 (New): The semiconductor die of claim 60, wherein the blade comprises a sharpened cutting edge along the length thereof.

Claim 69 (New): The semiconductor die of claim 60, wherein the blade comprises a first tapered portion and a second taper portion, wherein the first tapered portion and the second tapered portion taper one towards the other to form a sharpened cutting edge along the length of the blade.

Claim 70 (New): The semiconductor die of claim 60, wherein the blade comprises tapered portions that form a sharpened cutting edge along the length of the blade.